

# DFM: It's all about *Flexibility*



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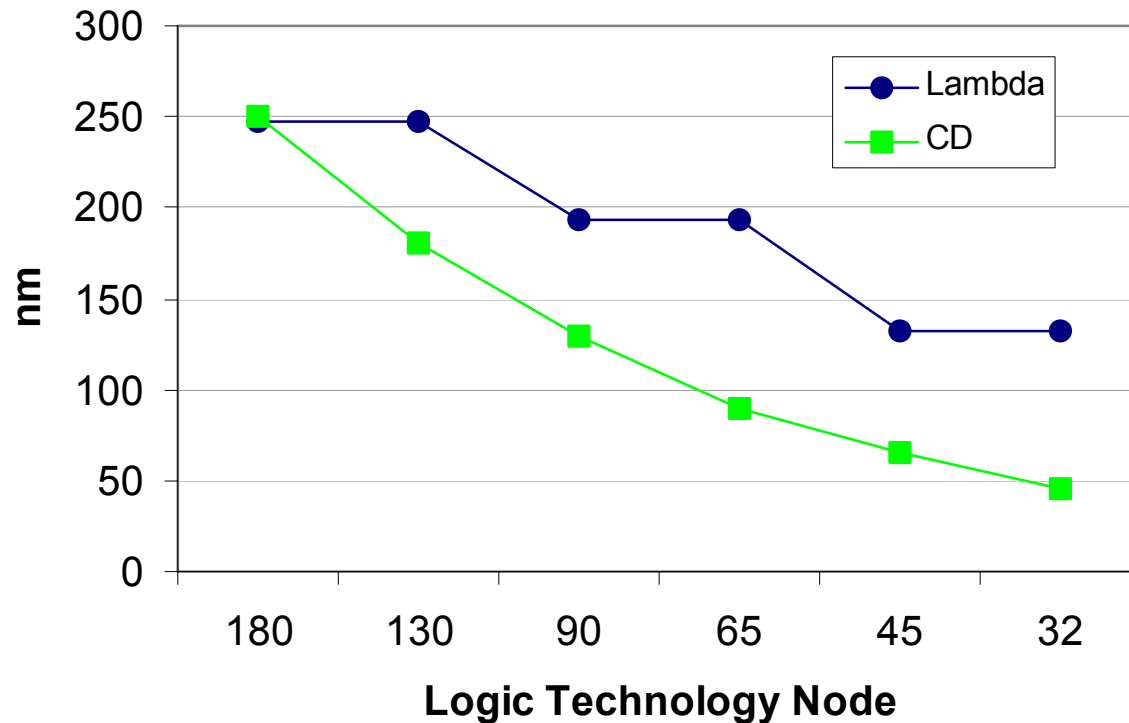
# Topics

- **Introduction**
  - Moore's law, scaling, the end of scaling
  - Photolithography, the subwavelength era
  - Resolution, knobs to turn
- **Cost**
  - Scanner cost trends; dry, wet, hyper
- **Design style**
  - Need to consider design and technology
  - 2D versus 1D design styles
  - RDR's and an additional  $k_1^*$  factor
- **Conclusions**

# Integrated Circuit Scaling

- **Moore's law**
  - Density of transistors doubles every  $n$  years ( $n=1, 1.5, 2, 3$ )
- **Scaling benefits**
  - Scaling laterally by 70% each generation (technology node) cuts the die area by 50%
  - Circuit frequency can increase, or power decrease
- **The end of scaling**
  - Transistor gate oxide thickness is limited by atomic spacing (we now count atomic layers in the dielectric)
  - Electrons can directly tunnel through thin barriers
  - These two factors are responsible for the power dissipation crisis we face today

# Photolithography: the subwavelength era



Patterning with  $\lambda$  less than the critical dimension creates a fidelity problem

# Optical Resolution

- **Rayleigh's equation**

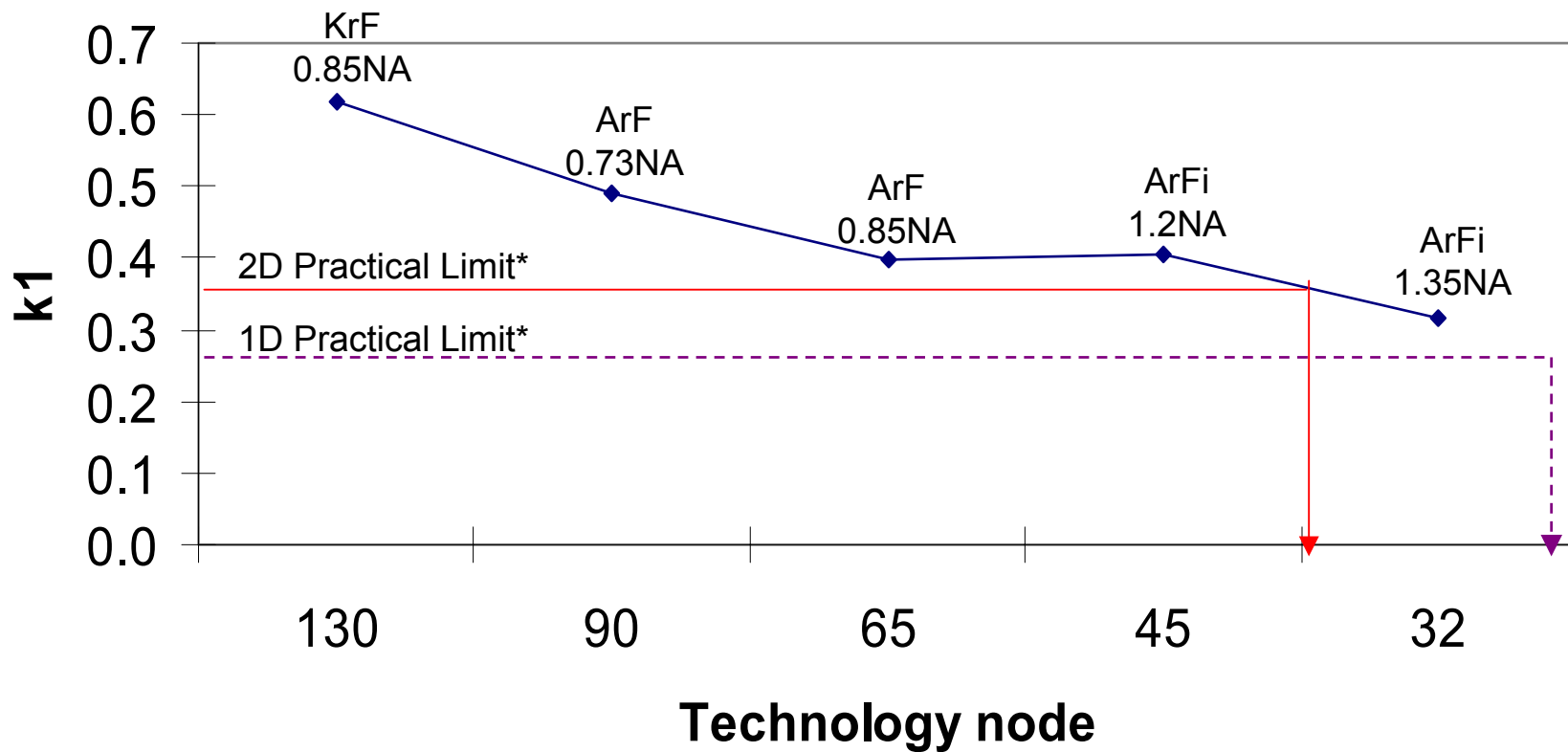
- **$CD = k_1 \lambda / NA$**

- **$k_1$  is the difficulty factor, lower is more difficult**
    - **$\lambda$  is the illumination wavelength; 193nm for ArF excimer laser**
    - **NA is the numerical aperture of the optical system**

- **Knobs to turn**

- **Patterning with lower  $k_1$  essentially means lower fidelity in the stepper requires higher capability in the resist process; in general, the contrast is lower so “chemically amplified” resists are needed**
  - **$\lambda$  is expensive to reduce, and nature gives few choices (the next choice, the F<sub>2</sub> excimer at 157 nm, was dropped from the roadmap)**
  - **NA has steadily increased, but the size and cost of the lens grows quickly with higher NA**

# $k_1$ trend



For each successive technology node in the subwavelength era, the difficulty factor has been approaching the practical limits.

\* Bill Arnold (ASML), IEDM 2006 32nm Short Course

# Patterning cost

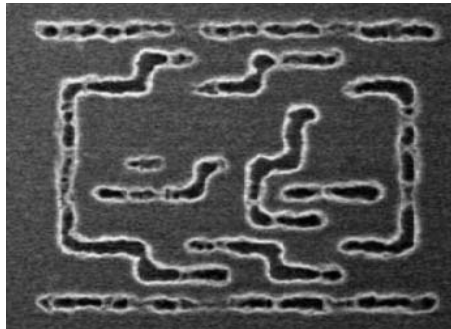
- **Stepper / scanner cost**
  - ~\$1M in 1986
  - ~25M in 2005
  - The decrease in  $\lambda$  and increase in NA have come at a cost, but until now the increase in cost has been offset by a decrease in die size
  - It is not clear that next generation steppers with  $NA > 1.3$  are feasible and can be cost effective
- **Impact of reduced fidelity**
  - Even with improved steppers,  $k_1$  has decreased steadily from  $k_1 > 0.6$  to  $k_1 < 0.4$ .
  - OPC (optical proximity correction) has been used to try to improve pattern fidelity
  - Unfortunately, even with OPC, low  $k_1$  results in “hot spots” in the design which may not be correctable

# Design – Technology interaction

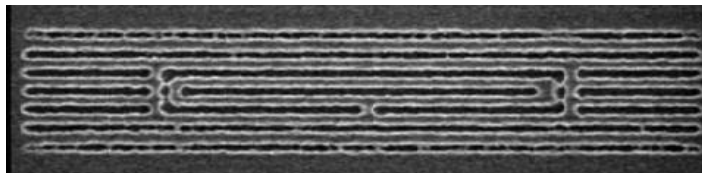
- **Morris Chang, founder of TSMC, at ISSCC 2007:**  
“deeper and broader relationships with customers are needed, covering both design and technology engineering to allow for increasing demands for product-cost performance and reduced time-to-market”
- **The traditional approach of using binary (pass/fail) design rules to communicate patterning capability from a fab to a design team is no longer enough to ensure a yieldable design**
- **An emerging factor is design style, in which how rules are used becomes important**



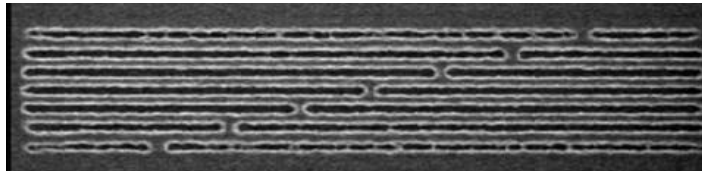
# Design styles



- Traditional 2D layout with bends, bi-directional shapes



- 2D layout with restrictions (RDR)



- 1D layout

Even though  $k_1 = 0.31$  in all cases, the fidelity of the 1D layout is better. Note that the 2D layout with restrictions still had problems at the bends.

SEMs from Applied Materials SPIE 2007 poster.

# Conclusions

- **Chip yield depends on the fidelity of the design layout replicated on wafers.**
- **The industry is clearly at a cross-roads, where the cost of photolithography is limiting lateral scaling; major players have dropped out of the race at 32nm.**
- **Even with RDR's, the needed patterning fidelity may be beyond economic limits at 45nm and below.**
- **Design style, for example more use of 1D patterns, is an important factor to consider to allow further scaling.**

# Acknowledgements

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- **Former colleagues at Applied Materials for their input to the SPIE 2007 poster SEMs**